



### **Product Summary**

| BV <sub>DSS</sub> | R <sub>DS(ON)</sub> MAX        | Package | I <sub>D</sub><br>T <sub>A</sub> = +25°C |
|-------------------|--------------------------------|---------|--|
|                   | 38mΩ @ V <sub>GS</sub> = -10V  |         | -4.3A                                    |
| -20V              | 43mΩ @ V <sub>GS</sub> = -4.5V | SOT23   | -4.0A                                    |
|                   | 75mΩ @ V <sub>GS</sub> = -2.5V |         | -2.8A                                    |

### Description

This new generation MOSFET is designed to minimize the on-state resistance ( $R_{DS(ON)}$ ) and yet maintain superior switching performance, making it ideal for high efficiency power management applications.

## **Applications**

- Load Switch
- Power Management Functions

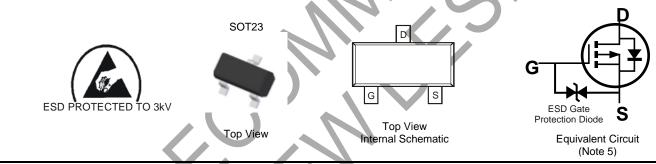
### P-CHANNEL ENHANCEMENT MODE MOSFET

#### Features

- Low On-Resistance
- Low Input Capacitance
- Fast Switching Speed
- Low Input/Output Leakage
- ESD Protected Up To 3kV
- Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)
- Qualified to AEC-Q101 Standards for High Reliability
- PPAP Capable (Note 4)

## **Mechanical Data**

- Case: SOT23
- Case Material: Molded Plastic, "Green" Molding Compound.
  UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals: Finish Matte Tin Annealed over Copper Leadframe. Solderable per MIL-STD-202, Method 208 (3)
- Terminals Connections: See Diagram Below
- Weight: 0.008 grams (Approximate)



## Ordering Information (Notes 5 & 6)

| Pa   | art Number  | Compliance | Case  | Packaging         |  |  |  |
|--|-------------|------------|-------|-------------------|--|--|--|
| D  | MP2100U-7   | Standard   | SOT23 | 3,000/Tape & Reel |  |  |  |
| DN   | /IP2100UQ-7 | Automotive | SOT23 | 3,000/Tape & Reel |  |  |  |
| Notes: 1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS), 2011/65/EU (RoHS 2) & 2015/863/EU (RoHS 3) compliant. |             |            |       |                   |  |  |  |

No purposely added lead. Fully EU Directive 2002/95/EC (RoHS), 2011/65/EU (RoHS 2) & 2015/863/EU (RoHS 3) compliant.
 See https://www.diodes.com/quality/lead-free/ for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.

Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.

 Automotive products are AEC-Q101 qualified and are PPAP capable. Automotive, AEC-Q101 and standard products are electrically and thermally the same, except where specified. For more information, please refer to https://www.diodes.com/quality/.

5. The ESD gate protection diode is only designed to protect against ESD events. No gate-source voltage greater than the maximum V<sub>GSS</sub> rating (given on page 2) can be applied.

6. For packaging details, go to our website at https://www.diodes.com/design/support/packaging/diodes-packaging/.

# **Marking Information**

| 35P | ΥM | 35P = Pro<br>YM = Date<br>Y = Year (<br>M = Month |
|-----|----|---|
|     |    |   |

35P = Product Type Marking Code YM = Date Code Marking

Y = Year (ex: F = 2018)

M = Month (ex: 9 = September)

| Date | Code | Key |
|------|------|-----|
|      |      |     |

| Year     | 2008 | ~   | 2017 | 2018 | 3 201 | 9 2    | 2020 | 2021 |    | 2022 | 2023 | 2024 | 2025        |
|----------|------|-----|------|------|-------|--------|------|------|----|------|------|------|-------------|
| Code     | V    | ~   | E    | F    | G     |        | Н    |      |    | J    | K    | L    | М           |
| Month    | Jan  | Feb | Mar  | Apr  | Мау   | Jun    | J    | ul A | ug | Sep  | Oct  | Nov  | Dec         |
| Code     | 1    | 2   | 3    | 4    | 5     | 6      | -    | 7    | 8  | 9    | 0    | N    | D           |
| DMP2100U |      |     |      |      | 1     | l of 6 |      |      |    |      |      | Fel  | oruary 2018 |



DMP2100U

# Maximum Ratings (@T<sub>A</sub> = +25°C, unless otherwise specified.)

| Characteristic                                    | Symbol           | Value  | Unit            |              |   |
|---|------------------|--|-----------------|--------------|---|
| Drain-Source Voltage                              | V <sub>DSS</sub> | -20  | V               |              |   |
| Gate-Source Voltage (Note 7)                      | V <sub>GSS</sub> | ±10  | V               |              |   |
|   | Steady<br>State  | T <sub>A</sub> = +25°C<br>T <sub>A</sub> = +70°C | I <sub>D</sub>  | -4.3<br>-3.4 | А |
| Continuous Drain Current (Note 9) $V_{GS} = -10V$ | t<5s             | T <sub>A</sub> = +25°C<br>T <sub>A</sub> = +70°C | I <sub>D</sub>  | -5.5<br>-4.3 | А |
| Maximum Continuous Body Diodes Forward Curr       | ent (Note 9      | )  | ls              | -2           | А |
| Pulsed Drain Current (10µs Pulse, Duty Cycle = 1  | 1%)              |  | I <sub>DM</sub> | -30          | А |
| Pulsed Body Diodes Forward Current (10µs Pulse    | e, Duty Cyc      | I <sub>SM</sub>                                  | -30             | А            |   |

# **Thermal Characteristics**

| Characteristic                                   |  |     | Symbol           | Value       | Unit |
|--|--|-----|------------------|-------------|------|
| Total Power Dissipation (Note 8)                 | T <sub>A</sub> = +25°C<br>T <sub>A</sub> = +70°C |     | PD               | 0.8         | W    |
| Thermal Resistance, Junction to Ambient (Note 8) | Steady State<br>t<5s                             |     | R <sub>0JA</sub> | 161<br>96   | °C/W |
| Total Power Dissipation (Note 9)                 | $T_A = +25^{\circ}C$<br>$T_A = +70^{\circ}C$     |     | PD               | 1.3<br>0.8  | W    |
| Thermal Resistance, Junction to Ambient (Note 9) | Steady State<br>t<5s                             |     | R <sub>0JA</sub> | 99<br>60    | °C/W |
| Thermal Resistance, Junction to Case (Note 9)    |  | . ( | R <sub>0JC</sub> | 15          |      |
| Operating and Storage Temperature Range          |  |     | TJ, TSTG         | -55 to +150 | °C   |

# Electrical Characteristics (@T<sub>A</sub> = +25°C, unless otherwise specified.)

| Characteristic                      | Symbol                   | Min  | Тур | Max  | Unit  | Test Condition  |  |  |
|-------------------------------------|--------------------------|------|-----|------|-------|---|--|--|
| OFF CHARACTERISTICS (Note 10)       |                          |      |     |      |       |   |  |  |
| Drain-Source Breakdown Voltage      | <b>BV</b> <sub>DSS</sub> | -20  |     | _    | V     | $V_{GS} = 0V, I_D = -250\mu A$  |  |  |
| Zero Gate Voltage Drain Current     | IDSS                     |      | -   | -1   | μA    | $V_{DS} = -20V, V_{GS} = 0V$  |  |  |
| Gate-Source Leakage                 | IGSS                     |      | —   | ±10  | μA    | $V_{GS} = \pm 8V, V_{DS} = 0V$  |  |  |
| ON CHARACTERISTICS (Note 10)        |                          |      |     |      |       |   |  |  |
| Gate Threshold Voltage              | V <sub>GS(TH)</sub>      | -0.3 |     | -1.4 | V     | $V_{DS} = V_{GS}, I_{D} = -250 \mu A$                                   |  |  |
|                                     |                          | -    | 25  | 38   |       | V <sub>GS</sub> = -10V, I <sub>D</sub> = -3.5A                          |  |  |
| Static Drain-Source On-Resistance   | D                        | -    | 29  | 43   | mΩ    | $V_{GS} = -4.5V, I_D = -3A$   |  |  |
| Static Drain-Source On Resistance   | RDS(ON)                  |      | 37  | 75   | 11122 | $V_{GS} = -2.5V, I_D = -1A$   |  |  |
|                                     |                          |      | 47  |      |       | $V_{GS} = -1.8V, I_D = -0.5A$   |  |  |
| Forward Transfer Admittance         | Y <sub>fs</sub>          |      | 3   |      | S     | $V_{DS} = -5V, I_D = -4A$   |  |  |
| DYNAMIC CHARACTERISTICS (Note 11)   |                          |      |     |      |       |   |  |  |
| Input Capacitance                   | Ciss                     |      | 216 | _    | рF    |   |  |  |
| Output Capacitance                  | Coss                     | _    | 90  | —    | pF    | V <sub>DS</sub> = -15V, V <sub>GS</sub> = 0V<br>f = 1.0MHz              |  |  |
| Reverse Transfer Capacitance        | Crss                     |      | 24  | _    | pF    |   |  |  |
| Gate Resistnace                     | Rg                       |      | 250 | _    | Ω     | $V_{DS} = 0V, V_{GS} = 0V, f = 1.0MHz$                                  |  |  |
| SWITCHING CHARACTERISTICS (Note 11) |                          |      |     |      |       |   |  |  |
| Total Gate Charge                   | Qg                       |      | 9.1 |      | nC    |   |  |  |
| Gate-Source Charge                  | Q <sub>gs</sub>          |      | 1.6 | -    | nC    | V <sub>GS</sub> = -4.5V, V <sub>DS</sub> = -10V<br>I <sub>D</sub> = -4A |  |  |
| Gate-Drain Charge                   | Q <sub>gd</sub>          |      | 2.0 | _    | nC    | $I_D = -4A$   |  |  |
| Turn-On Delay Time                  | t <sub>D(ON)</sub>       |      | 80  | _    | ns    |   |  |  |
| Turn-On Rise Time                   | t <sub>R</sub>           |      | 155 | —    | ns    | $V_{DS} = -10V, V_{GS} = -4.5V,$  |  |  |
| Turn-Off Delay Time                 | t <sub>D(OFF)</sub>      |      | 688 | _    | ns    | $R_{D} = 2.5\Omega, R_{G} = 3.0\Omega$                                  |  |  |
| Turn-Off Fall Time                  | t <sub>F</sub>           |      | 423 | _    | ns    |   |  |  |

7. AEC-Q101  $V_{GS}$  maximum is  $\pm 9.6V.$ Notes:

8. Device mounted on FR-4 substrate PC board, 2oz copper, with minimum recommended pad layout.
 9. Device mounted on FR-4 substrate PC board, 2oz copper, with 1inch square copper plate.

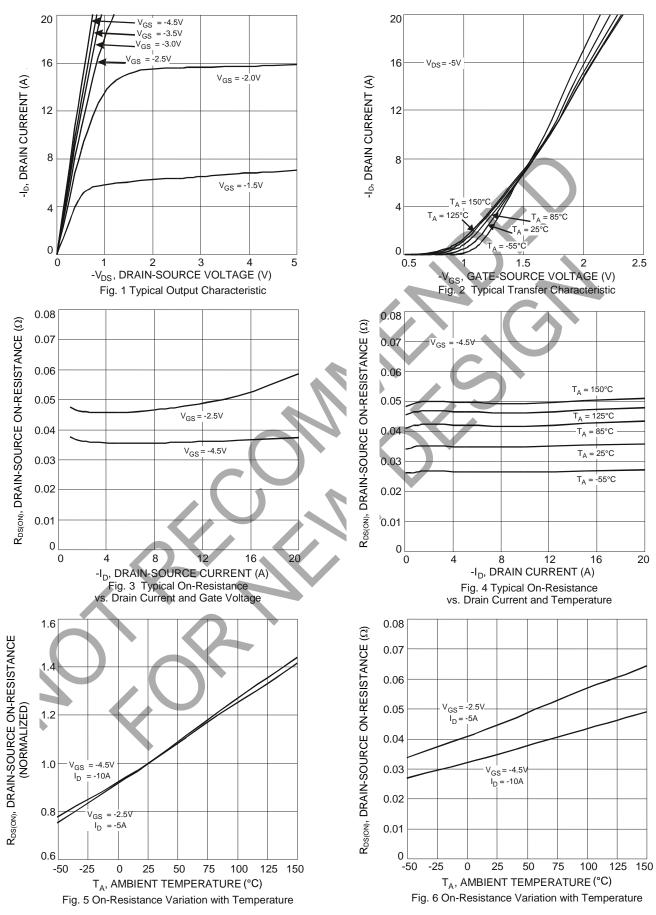
10. Short duration pulse test used to minimize self-heating effect.

11. Guaranteed by design. Not subject to product testing.



### NOT RECOMMENDED FOR NEW DESIGN USE <u>DMP2045U</u>

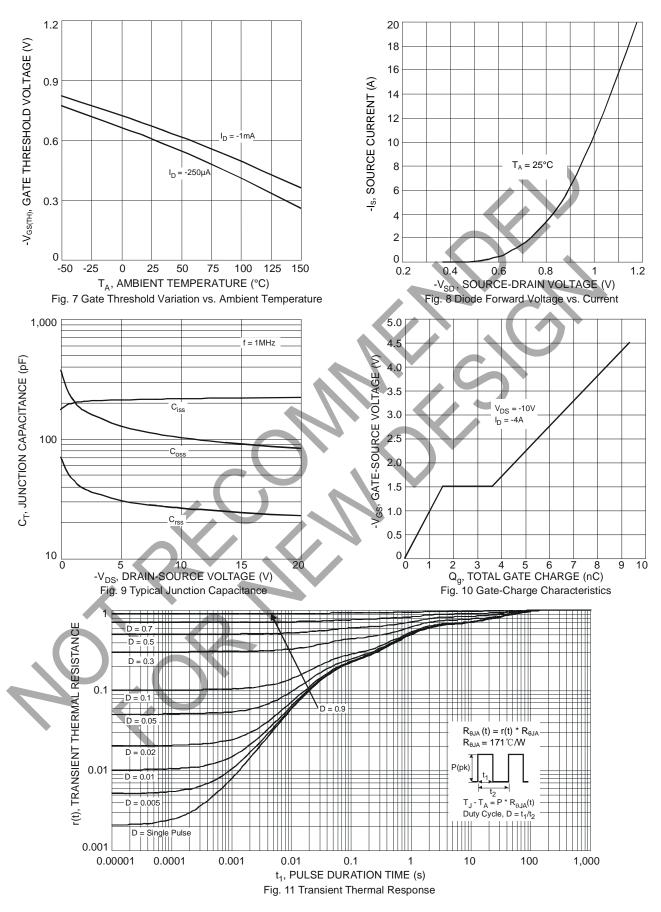
DMP2100U





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DMP2100U

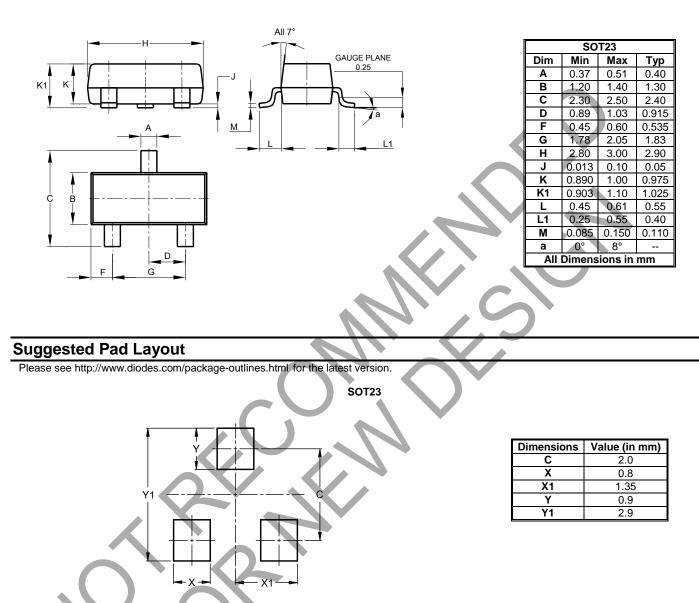




### Package Outline Dimensions

Please see http://www.diodes.com/package-outlines.html for the latest version.

SOT23





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